

Diodes

Schottky barrier diode

RB715W / RB715F

●Applications

General purpose detection  
 High speed switching

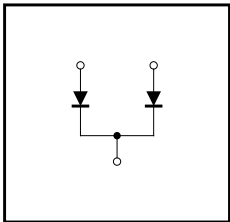
●Features

- 1) Small surface mounting type.  
(EMD3, UMD3)
- 2) Low  $V_F$  and low  $I_R$
- 3) High reliability

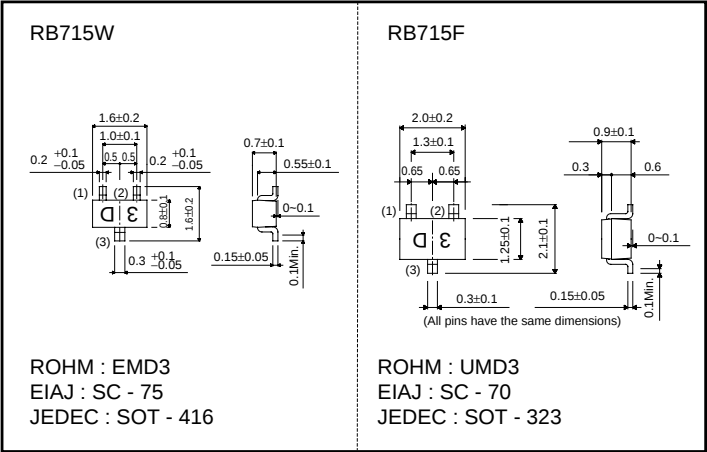
●Construction

Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

| Parameter                   | Symbol    | Limits   | Unit |
|-----------------------------|-----------|----------|------|
| Peak reverse voltage        | $V_{RM}$  | 40       | V    |
| DC reverse voltage          | $V_R$     | 40       | V    |
| Mean rectifying current     | $I_o$     | 30       | mA   |
| Peak forward surge current* | $I_{FSM}$ | 200      | mA   |
| Junction temperature        | $T_j$     | 125      | °C   |
| Storage temperature         | $T_{stg}$ | -40~+125 | °C   |

\* 60 Hz for 1 ms

●Electrical characteristics (Ta=25°C)

| Parameter                     | Symbol | Min. | Typ. | Max. | Unit    | Conditions       |
|-------------------------------|--------|------|------|------|---------|------------------|
| Forward voltage               | $V_F$  | —    | —    | 0.37 | V       | $I_F=1mA$        |
| Reverse current               | $I_R$  | —    | —    | 1    | $\mu A$ | $V_R=10V$        |
| Capacitance between terminals | $C_T$  | —    | 2.0  | —    | pF      | $V_R=1V, f=1MHz$ |

Note) ESD sensitive product handling required.

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●Electrical characteristic curves (Ta=25°C)

